

J ournal of I ntegrated C ircuits and S ystems

Volume 11 • Number 1 • April 2016 • ISSN 1807-1953

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An Analytical Study Of Temperature Dependence of Scaled CMOS Digital Circuits Using α -Power MOSFET Model

S. Kalra and A. B. Bhattacharyya



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Journal of **I**ntegrated **C**ircuits and **S**ystems

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FOREWORD

We are pleased to publish the 2016 issues of JICS, which represents the second year in the path to increase visibility and attraction of high quality papers, by publishing three issues instead of two.

In this issue one can find some of the papers that have been selected from those presented at SBMicro2015 (30th Symposium on Microelectronics Technology and Devices) and SBCCI2015 SBCCI2014 (28th Symposium on Integrated Circuits and Systems Design), which have been held in Salvador, Brazil, in 2015. Among the contributions presented at both Symposia, only a few best rated were selected by the JICS Editorial Board and have been invited to submit an extended version to the Journal. These extended papers have passed through the usual reviewing process before acceptance.

In addition to the best papers presented at these conference, spontaneous submissions passed through the usual reviewing process and have been accepted as regular papers.

We would like to thank the authors for their effort in preparing these high quality papers, as well as the reviewers for their valuable contribution on paper evaluation and selection, which guarantees the scientific level of this issue. We sincerely hope that JICS readers will enjoy these contributions.

Marcelo Antonio Pavanello
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